

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the subject application.

1. (Currently Amended) A light emitting display device comprising:
a base film including a substance with a photocatalytic function formed on a substrate;
a gate electrode formed [[on]] over and in direct contact with the base film;
a gate insulating layer formed over the gate electrode;
a semiconductor layer and a first electrode formed over the gate insulating layer;
a wiring layer formed over the semiconductor layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the wiring layer covers the edge portion of the first electrode.

2. (Currently Amended) A light emitting display device comprising:
a base film including a substance with a photocatalytic function formed on a substrate;
a wiring layer and a first electrode formed [[on]] over and in direct contact with the base film;
a semiconductor layer formed over the wiring layer;
a gate insulating layer formed over the semiconductor layer;
a gate electrode formed over the gate insulating layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the wiring layer covers the edge portion of the first electrode.

3. (Currently Amended) A light emitting display device comprising:

a base film including a substance with a photocatalytic function formed on a substrate;

- a gate electrode formed ~~[[on]]~~ over and in direct contact with the base film;
- a gate insulating layer formed over the gate electrode;
- a semiconductor layer and a first electrode formed over the gate insulating layer;
- a wiring layer formed over the semiconductor layer;
- a partition wall covering an edge portion of the first electrode and the wiring layer;
- an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,

wherein the first electrode covers an edge portion of the wiring layer.

4. (Currently Amended) A light emitting display device comprising:

a base film including a substance with a photocatalytic function formed on a substrate;

~~a gate electrode~~ a wiring layer and a first electrode formed ~~[[on]]~~ over and in direct contact with the base film;

- a semiconductor layer formed over the wiring layer;
- a gate insulating layer formed over the semiconductor layer;
- a gate electrode formed over the gate insulating layer;
- a partition wall covering an edge portion of the first electrode and the wiring layer;
- an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,

wherein the first electrode covers an edge portion of the wiring layer.

5. (Currently Amended) A light emitting display device according to any one of claims 1 to 4, wherein the substance having ~~[[a]]~~ the photocatalytic function comprises titanium oxide.

6. (Currently Amended) A light emitting display device comprising:

- a conductive layer including a refractory metal over a substrate having an insulating surface;
- a gate electrode formed over and in direct contact with the conductive layer;

a gate insulating layer formed over the gate electrode;
a semiconductor layer and a first electrode formed over the gate insulating layer;
a wiring layer formed over the semiconductor layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the wiring layer covers the edge portion of the first electrode.

7. (Currently Amended) A light emitting display device comprising:
a conductive layer including a refractory metal over a substrate having an insulating surface;
a wiring layer and a first electrode formed over and in direct contact with the conductive layer;
a semiconductor layer formed over the wiring layer;
a gate insulating layer formed over the semiconductor layer;
a gate electrode formed over the gate insulating layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the wiring layer covers the edge portion of the first electrode.

8. (Currently Amended) A light emitting display device comprising:
a conductive layer including a refractory metal over a substrate having an insulating surface;
a gate electrode formed over and in direct contact with the conductive layer;
a gate insulating layer formed over the gate electrode;
a semiconductor layer and a first electrode formed over the gate insulating layer;
a wiring layer formed over the semiconductor layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the first electrode covers an edge portion of the wiring layer.

9. (Currently Amended) A light emitting display device comprising:
a conductive layer including a refractory metal over a substrate having an insulating surface;
a wiring layer and a first electrode formed over and in direct contact with the conductive layer;
a semiconductor layer formed over the wiring layer;
a gate insulating layer formed over the semiconductor layer;
a gate electrode formed over the gate insulating layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the first electrode covers an edge portion of the wiring layer.

10. (Previously Presented) A light emitting display device according to any one of claims 6 to 9, wherein the refractory metal is selected from the group consisting of Ti (titanium), W (tungsten), Cr (chromium), Al (aluminum), Ta (tantalum), Ni (nickel), Zr (zirconium), Hf (hafnium), V (vanadium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Co (cobalt), and Rh (rhodium).

11. (Currently Amended) A light emitting display device according to any one of claims 1 to 4 and 6 to 9, wherein the gate electrode and the wiring layer are made of a material selected from the group consisting of silver, gold, copper, and indium tin oxide.

12. (Currently Amended) A light emitting display device according to any one of claims 1 to 4 and 6 to 9, wherein the semiconductor layer is a semi-amorphous semiconductor containing hydrogen and halogen and having a crystal structure.

13. (Currently Amended) A TV set including a display screen having the light emitting display device according to any one of claims 1 to 4 and 6 to 9.

14. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

- forming a base film including a substance with a photocatalytic function on a substrate;
- forming a gate electrode ~~[[on]]~~ over and in contact with the base film having an insulating surface by a first droplet discharge method;
- forming a gate insulating layer over the gate electrode;
- forming a semiconductor layer over the gate insulating layer;
- forming a first electrode over the gate insulating layer by a second droplet discharge method;
- forming a wiring layer over the semiconductor layer by a third droplet discharge method to cover an edge portion of the first electrode;
- forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
- forming an electroluminescent layer over the first electrode; and
- forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

15. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

- forming a base film including a substance with a photocatalytic function on a substrate;
- forming a ~~[[gate]]~~ first electrode ~~[[on]]~~ over and in direct contact with the base film having an insulating surface by a first droplet discharge method;
- forming a wiring layer over and in contact with ~~the substrate~~ the base film having ~~[[an]]~~ the insulating surface ~~with a substance having a photocatalytic function therebetween~~ by a second droplet discharge method to cover an edge portion of the first electrode;
- forming a semiconductor layer over the wiring layer;
- forming a gate insulating layer over the semiconductor layer;
- forming a gate electrode over the gate insulating layer by a third droplet discharge method;

forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

16. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a base film including a substance with a photocatalytic function on a substrate;

forming a gate electrode in direct contact with the base film having an insulating surface by a first droplet discharge method;

forming a gate insulating layer over the gate electrode;
forming a semiconductor layer over the gate insulating layer;
forming a wiring layer over the semiconductor layer by a second droplet discharge method;

forming a first electrode over the gate insulating layer by a third droplet discharge method to cover an edge portion of the wiring layer;

forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

17. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a base film including a substance with a photocatalytic function on a substrate;

forming a wiring layer over and in direct contact with the base film having an insulating surface by a first droplet discharge method;

forming a first electrode over and in direct contact with the base film having an insulating surface by a second droplet discharge method to cover an edge portion of the wiring layer;

forming a semiconductor layer over the wiring layer;
forming a gate insulating layer over the semiconductor layer;
forming a gate electrode over the gate insulating layer by a third droplet discharge method;
forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

18. (Currently Amended) A method for manufacturing a light emitting display device according to any one of claims 14 to 17, wherein titanium oxide is used as the substance having [[a]] the photocatalytic function.

19. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;
forming a gate electrode over and in direct contact with the conductive layer by a first droplet discharge method;
forming a gate insulating layer over the gate electrode;
forming a semiconductor layer over the gate insulating layer;
forming a first electrode over the gate insulating layer by a second droplet discharge method;
forming a wiring layer over the semiconductor layer by a third droplet discharge method to cover an edge portion of the first electrode;
forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and

forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

20. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;

forming a first electrode over and in direct contact with the conductive layer by a first droplet discharge method;

forming a wiring layer over and in direct contact with the conductive layer by a second droplet discharge method to cover an edge portion of the first electrode;

forming a semiconductor layer over the wiring layer;

forming a gate insulating layer over the semiconductor layer;

forming a gate electrode over the gate insulating layer by a third droplet discharge method;

forming a partition wall to cover the edge portion of the first electrode and the wiring layer;

forming an electroluminescent layer over the first electrode; and

forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

21. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;

forming a gate electrode over and in direct contact with the conductive layer by a first droplet discharge method;

forming a gate insulating layer over the gate electrode;

forming a semiconductor layer over the gate insulating layer;

forming a wiring layer over the semiconductor layer by a second droplet discharge method;

forming a first electrode over the gate insulating layer by a third droplet discharge method to cover an edge portion of the wiring layer;
forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

22. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;
forming a wiring layer over and in direct contact with the conductive layer by a first droplet discharge method;
forming a first electrode over and in direct contact with the conductive layer by a second droplet discharge method to cover an edge portion of the wiring layer;
forming a semiconductor layer over the wiring layer;
forming a gate insulating layer over the semiconductor layer;
forming a gate electrode over the gate insulating layer by a third droplet discharge method;
forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a fourth droplet discharge method.

23. (Previously Presented) A method for manufacturing a light emitting display device according to any one of claims 19 to 22,

wherein the refractory metal is selected from the group consisting of Ti (titanium), W (tungsten), Cr (chromium), Al (aluminum), Ta (tantalum), Ni (nickel), Zr (zirconium), Hf (hafnium), V (vanadium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Co (cobalt), and Rh (rhodium).

24. (Previously Presented) A method for manufacturing a light emitting display device according to any one of claims 14 to 17, 19 to 21, and 22,

wherein the gate electrode and the wiring layer comprise a material selected from the group consisting of silver, gold, copper, and indium tin oxide.

25. (Previously Presented) A method for manufacturing a light emitting display device according to any one of claims 14 to 17, 19 to 21, and 22,

wherein the semiconductor layer comprises a semi-amorphous semiconductor containing hydrogen and halogen and having a crystal structure.